



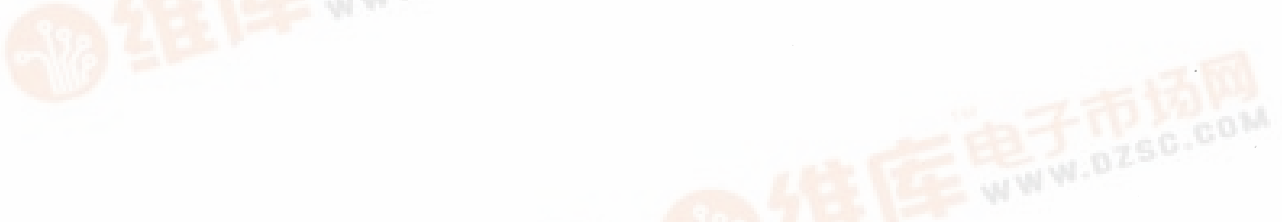
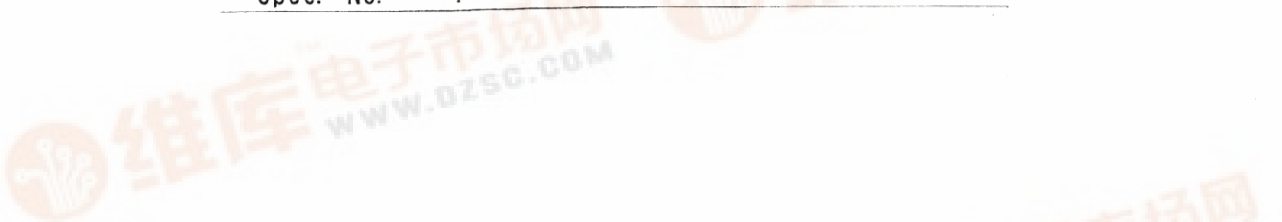
SPECIFICATION



Device Name : I G B T M o d u l e

Type Name : 6 M B I 5 0 S - 1 4 0

Spec. No. : M S 5 F 4 7 2 3



Fuji Electric Co., Ltd.
Matsumoto Factory

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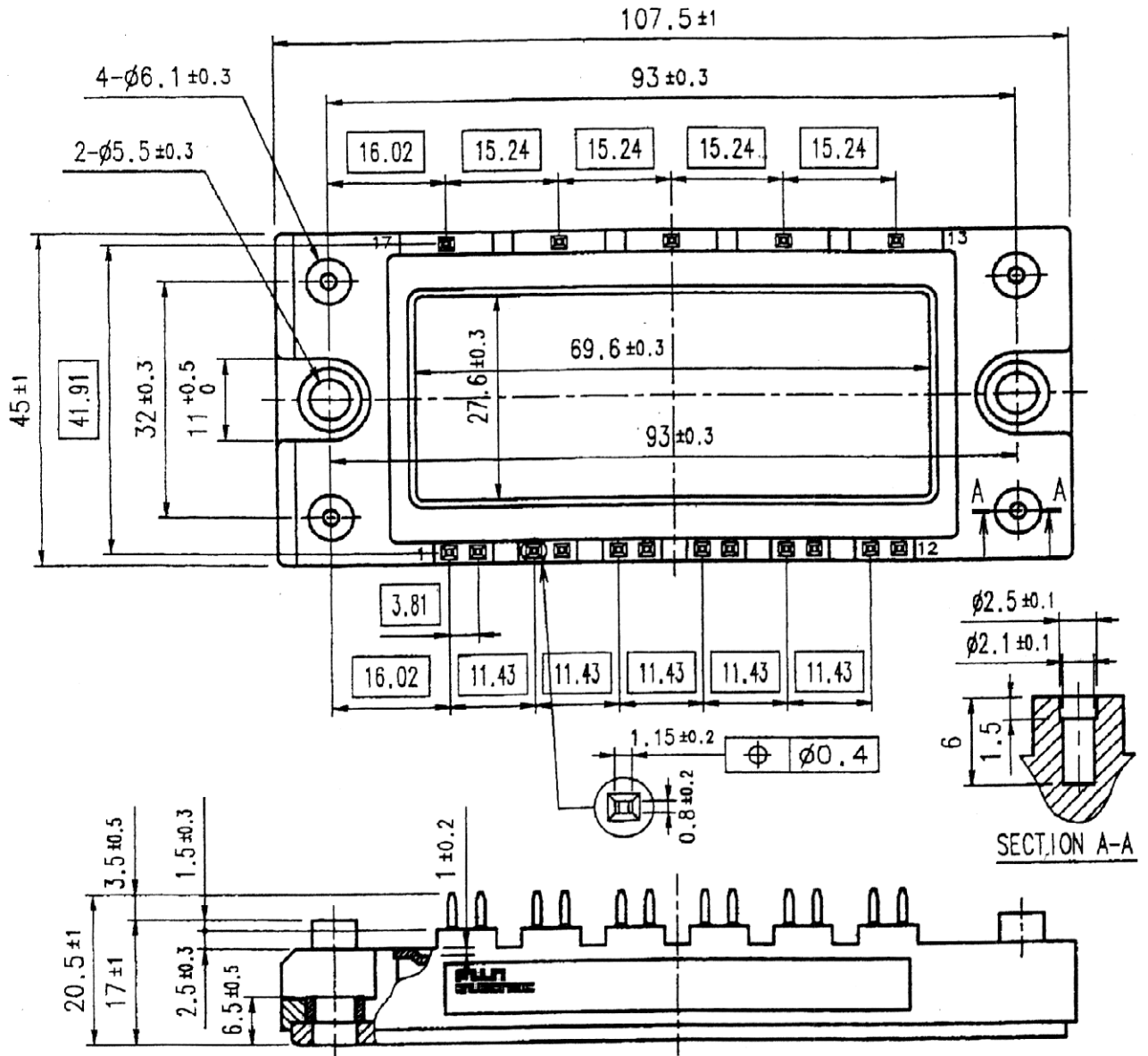


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Fuji Electric Co., Ltd.	
V.G. NO.	M S 5 F 4 7 2 3 1 / 8

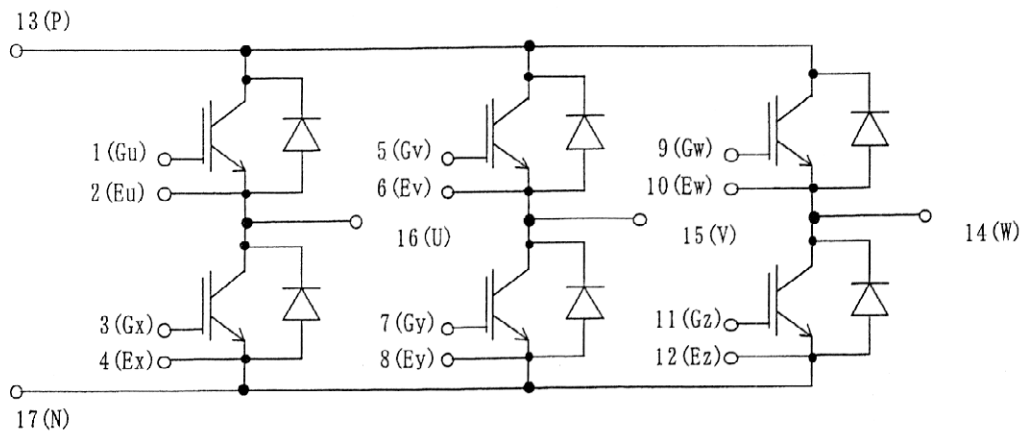
6 M B I 5 0 S - 1 4 0

1. Outline Drawing (Unit : mm)



□ shows theoretical dimension.

2. Equivalent circuit



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3. Absolute Maximum Ratings (at Tc= 25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum Ratings		Units
Collector-Emitter voltage	VCES		1400		V
Gate-Emitter voltage	VGES		±20		V
Collector current	Ic	Continuous	Tc=25°C	75	A
			Tc=75°C	50	
	Ic pulse	1ms	Tc=25°C	150	
			Tc=75°C	100	
	-Ic			50	
-Ic pulse		1ms	100		
Collector Power Dissipation	Pc	1 device	360		W
Junction temperature	Tj		150		°C
Storage temperature	Tstg		-40~ +125		°C
Isolation voltage ^(*1)	Viso	AC : 1min.	2500		V
Mounting Screw Torque ^(*2)			3.5		N·m

(*1) All terminals should be connected together when isolation test will be done.

(*2) Recommendable Value : 2.5~3.5 N·m (M5)

4. Electrical characteristics (at Tj= 25°C unless otherwise specified)

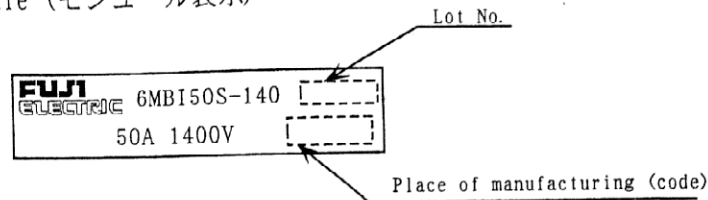
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Zero gate voltage Collector current	ICES	VGE = 0 V, VCE = 1400 V			1.0	mA
Gate-Emitter leakage current	IGES	VCE = 0 V, VGE = ±20 V			200	nA
Gate-Emitter threshold voltage	VGE(th)	VCE = 20 V, Ic = 50 mA	5.5	7.2	8.5	V
Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, Tj = 25 °C		2.4	2.75	V
		Ic = 50 A, Tj = 125 °C		3.0		
Input capacitance	Cies	VGE = 0 V		6000		pF
Output capacitance	Coes	VCE = 10 V		1250		
Reverse transfer capacitance	Cres	f = 1 MHz		1100		
Turn-on time	ton	Vcc = 800 V		0.35	1.2	μs
	tr	Ic = 50 A		0.25	0.6	
	tr(i)	VGE = ±15 V		0.1		
Turn-off time	toff	RG = 24 Ω		0.45	1.0	μs
	tf			0.08	0.3	
Forward on voltage	VF	IF = 50 A	Tj = 25 °C	2.6	3.4	V
			Tj = 125 °C	2.2		
Reverse recovery time	trr	IF = 50 A			0.35	μs

5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	IGBT			0.35	°C/W
		FWD			0.75	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound (※)		0.05		

※ This is the value which is defined mounting on the additional cooling fin

6. Indication on module (モジュール表示)



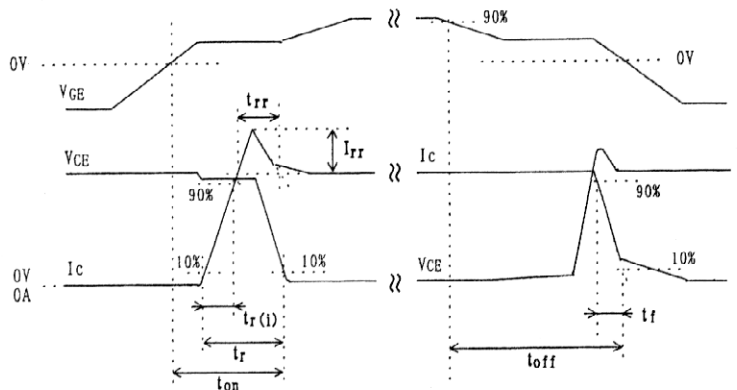
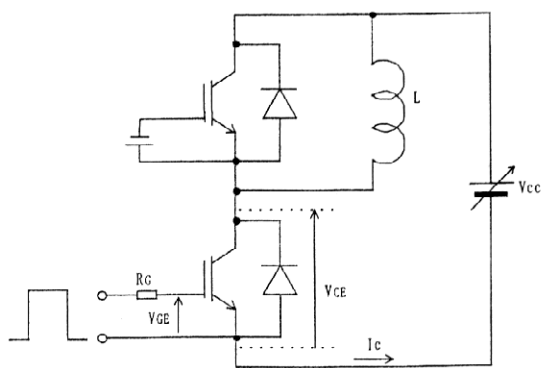
7. Applicable category (適用範囲)

This specification is applied to IGBT Module named 6MBI50S-140 .
 本納入仕様書は IGBTモジュール 6MBI50S-140 に適用する。

8. Storage and transportation notes (保管・運搬上の注意事項)

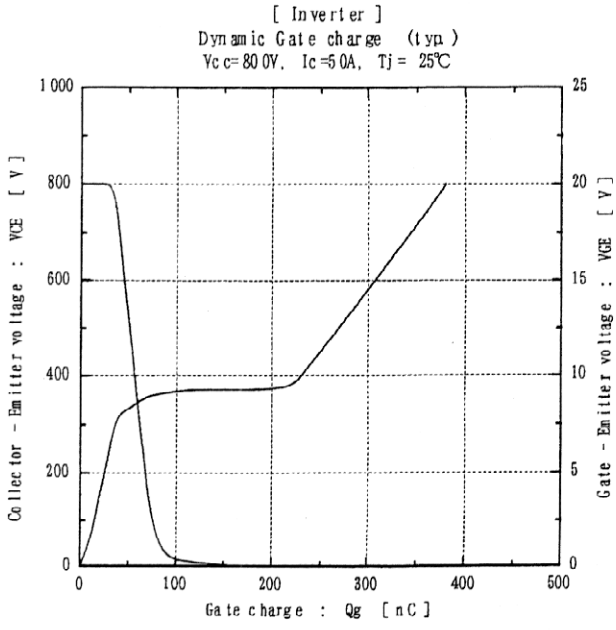
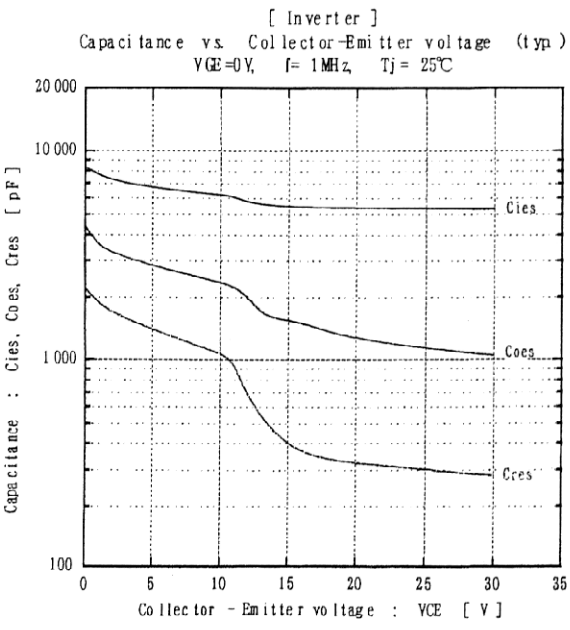
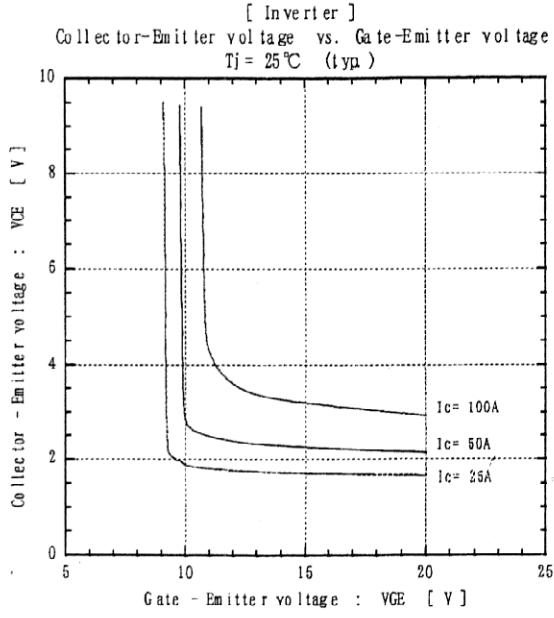
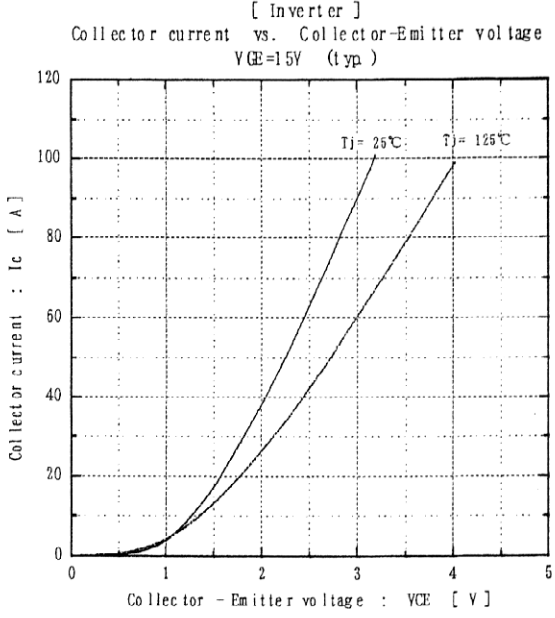
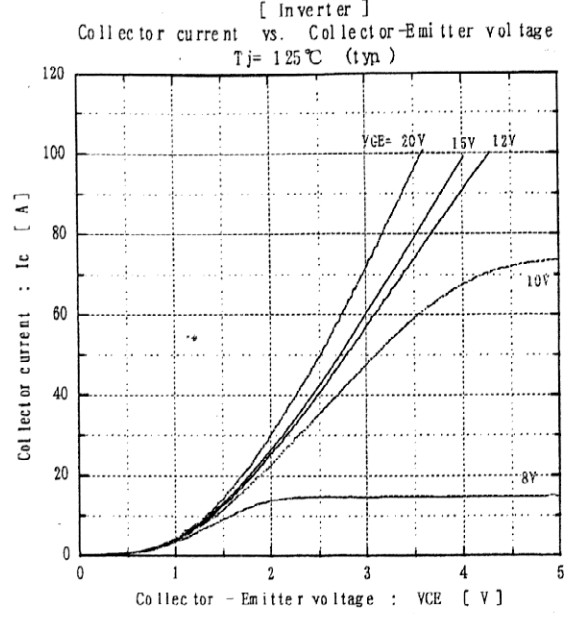
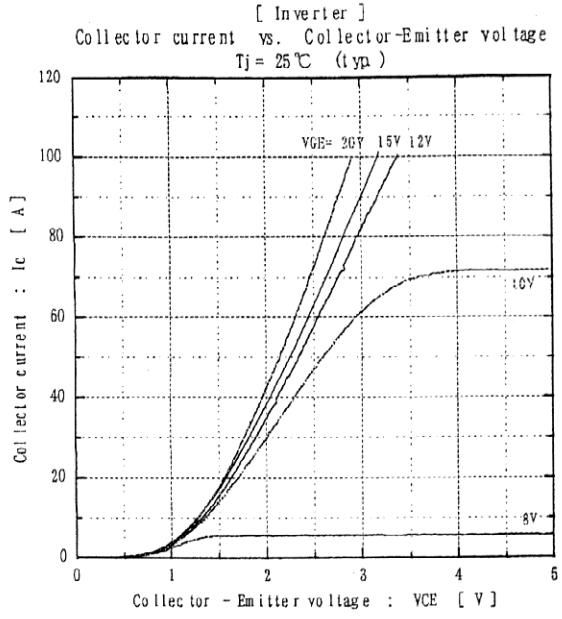
- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
 常温・常湿保存が望ましい。(5~35°C, 45~75%)
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
 急激な温度変化のなきこと。(モジュール表面が結露しないこと)
- Avoid exposure to corrosive gases and dust.
 腐蝕性ガスの発生場所, 塵埃の多い場所は避けること。
- Avoid excessive external force on the module.
 製品に荷重がかからないように 十分注意すること。
- Store modules with unprocessed terminals.
 モジュールの端子は未加工の状態 で保管すること。
- Do not drop or otherwise shock the modules when transporting.
 製品の運搬時に衝撃を与えたり、落下させたりしないこと。

9. Definitions of switching time (スイッチング時間の定義)

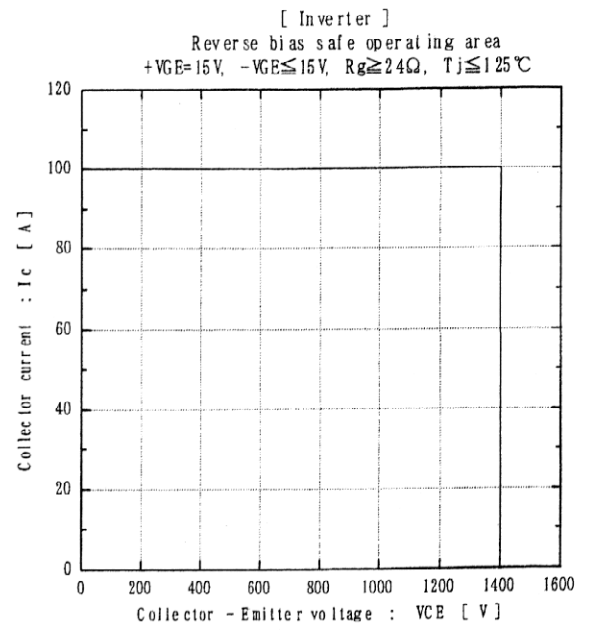
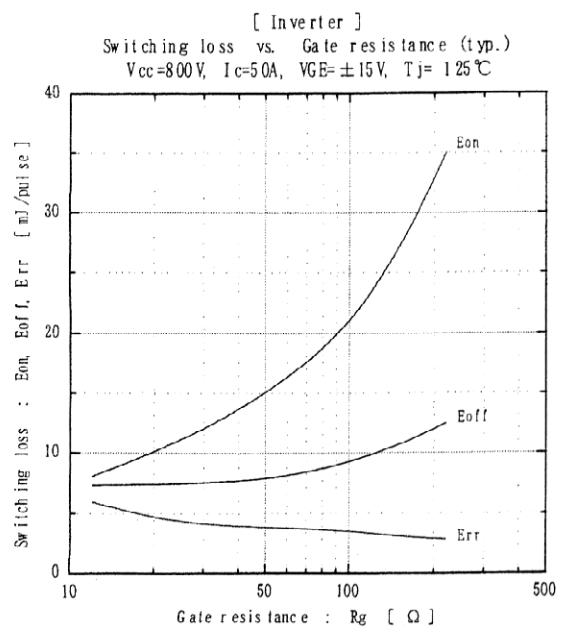
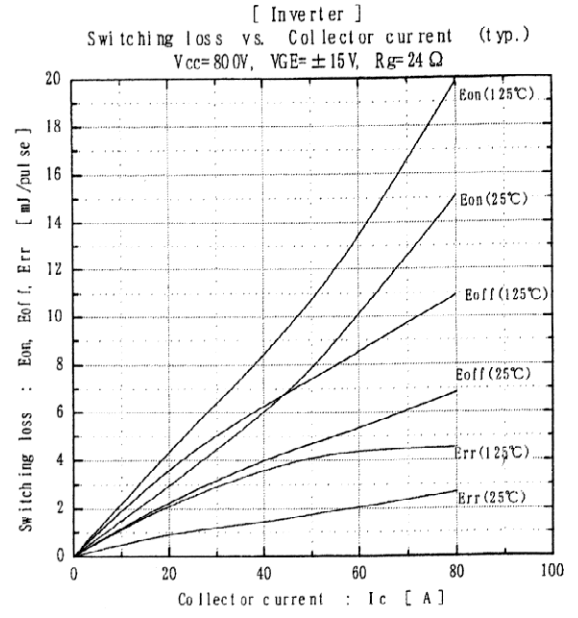
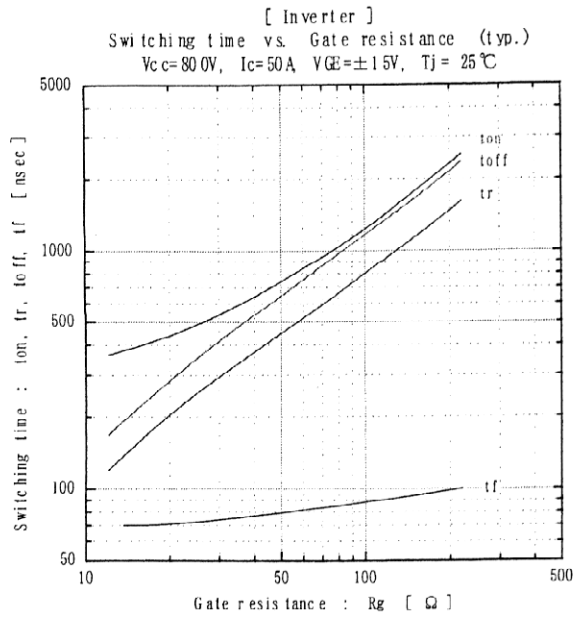
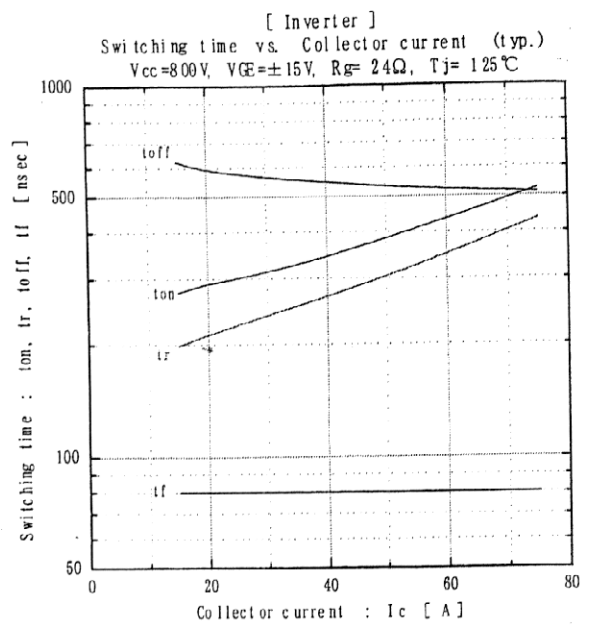
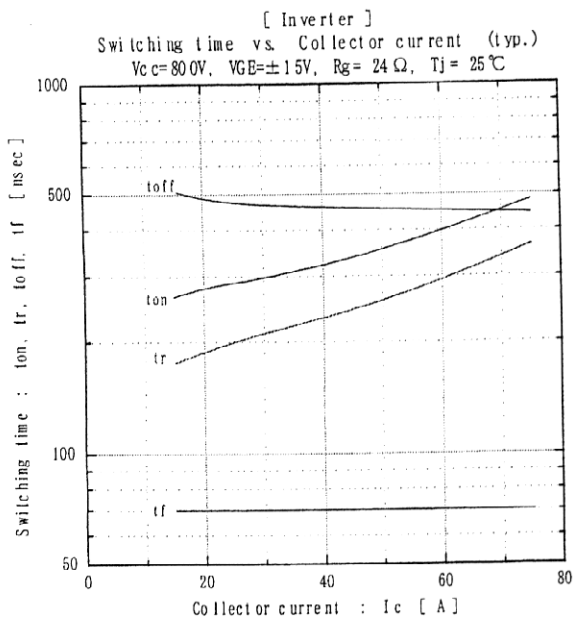


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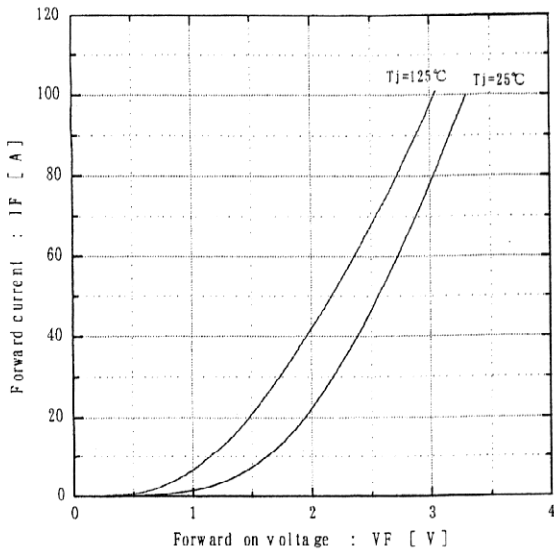
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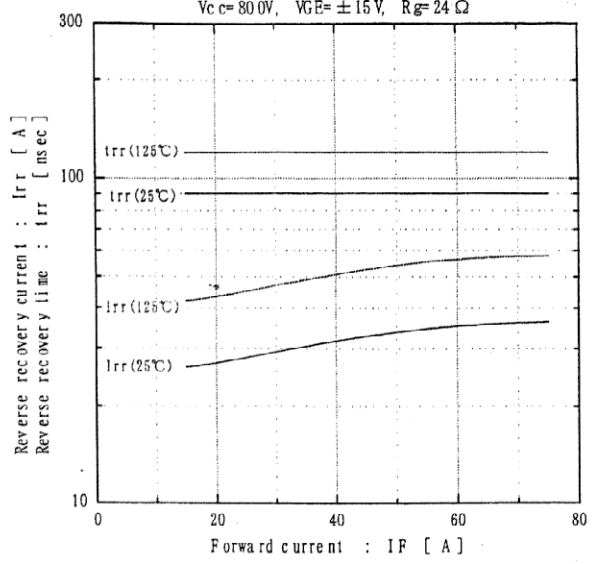
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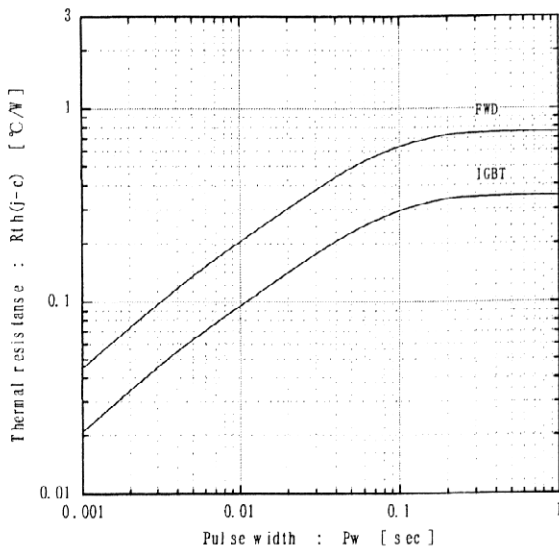
Forward current vs. Forward on voltage (typ.)



Reverse recovery characteristics (typ.)



Transient thermal resistance



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